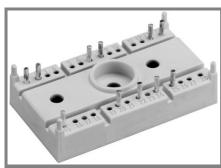
## **SK100WT**



SEMITOP®3

# Antiparallel Thyristor Module

#### SK100WT

**Preliminary Data** 

#### **Features**

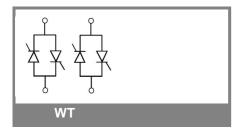
- Compact Design
- · One screw mounting
- Heat transfer and isolation trough direct copper bonded aluminium oxide ceramic (DCB)
- · Glass passived thyristor chips
- Up to 1600V reverse voltage
- UL recognized, file no. E 63 532

### **Typical Applications**

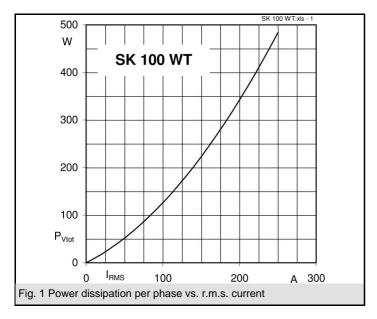
- Soft starters
- Light control (studios, theaters...)
- Temperature control

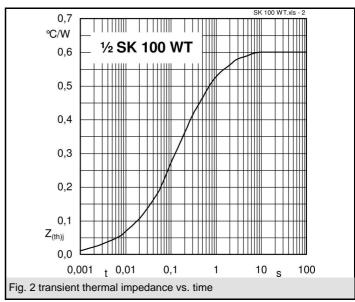
V <sub>RSM</sub> V	V <sub>RRM</sub> , V <sub>DRM</sub> V	I <sub>RMS</sub> = 101 A (full conduction) (T <sub>s</sub> = 85 °C)
900	800	SK 100 WT 08
1300	1200	Sk 100 WT 12
1700	1600	SK 100 WT 16

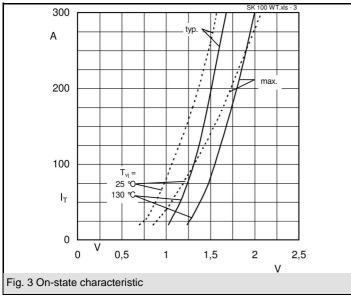
Symbol	Conditions	Values	Units
I <sub>RMS</sub>	W1C ; sin. 180° ; T <sub>s</sub> =100°C	71	Α
	W1C ; sin. 180° ; T <sub>s</sub> =85°C	101	Α
I <sub>TSM</sub>	T <sub>vi</sub> = 25 °C ; 10 ms	1500	Α
	T <sub>vi</sub> = 125 °C ; 10 ms	1350	Α
i²t	T <sub>vj</sub> = 25 °C ; 8,3 10 ms	11250	A²s
	T <sub>vj</sub> = 125 °C ; 8,3 10 ms	9100	A²s
V <sub>T</sub>	$T_{v_i} = 25  ^{\circ}\text{C}, I_T = 200  \text{A}$	max. 1,8	V
$V_{T(TO)}$	T <sub>vi</sub> = 125 °C	max. 0,9	V
r <sub>T</sub>	T <sub>vi</sub> = 125 °C	max. 4,5	mΩ
$I_{DD};I_{RD}$	$T_{vj} = 25  ^{\circ}\text{C},  V_{RD} = V_{RRM}$	max. 1	mA
	$T_{vj}$ = 125 °C, $V_{RD} = V_{RRM}$	max. 20	mA
t <sub>gd</sub>	$T_{vj}$ = 25 °C, $I_{G}$ = 1 A; $di_{G}/dt$ = 1 A/ $\mu$ s	1	μs
t <sub>gr</sub>	$V_D = 0.67 *V_{DRM}$	2	μs
(dv/dt) <sub>cr</sub>	T <sub>vi</sub> = 125 °C	1000	V/µs
(di/dt) <sub>cr</sub>	T <sub>vi</sub> = 125 °C; f= 50 60 Hz	50	A/µs
t <sub>q</sub>	T <sub>vi</sub> = 125 °C; typ.	80	μs
I <sub>H</sub>	T <sub>vi</sub> = 25 °C; typ. / max.	100 / 200	mA
$I_L$	$T_{vj} = 25 ^{\circ}\text{C};  R_{G} = 33 \Omega;  \text{typ. / max.}$	200 / 500	mA
V <sub>GT</sub>	$T_{vi} = 25 ^{\circ}\text{C}; \text{d.c.}$	min. 2	V
I <sub>GT</sub>	$T_{vi} = 25 ^{\circ}\text{C}; \text{d.c.}$	min. 100	mA
$V_{GD}$	$T_{vj}^{3}$ = 125 °C; d.c.	max. 0,25	V
$I_{GD}$	T <sub>vj</sub> = 125 °C; d.c.	max. 5	mA
$R_{th(j-s)}$	cont. per thyristor	0,6	K/W
	sin 180° per thyristor	0,63	K/W
$R_{th(j-s)}$	cont. per W1C	0,3	K/W
	sin 180° per W1C	0,315	K/W
$T_{vj}$		-40 <b>+12</b> 5	°C
T <sub>stg</sub>		-40 <b>+</b> 125	°C
T <sub>solder</sub>	terminals, 10 s	260	°C
V <sub>isol</sub>	a. c. 50 Hz; r.m.s.; 1 s / 1 min.	3000 / 2500	V~
M <sub>s</sub>		2,5	Nm
$M_t$			Nm
а			m/s²
m		30	g
Case	SEMITOP® 3	T 63	

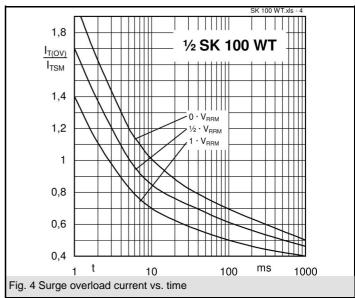


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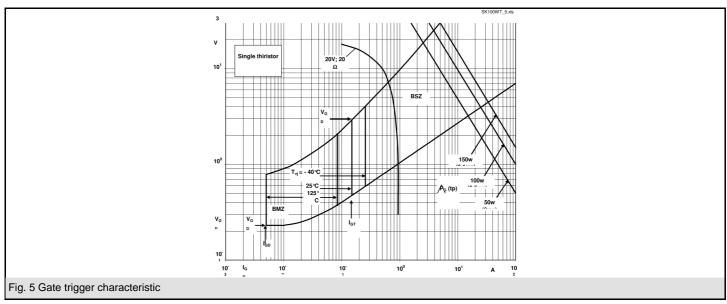


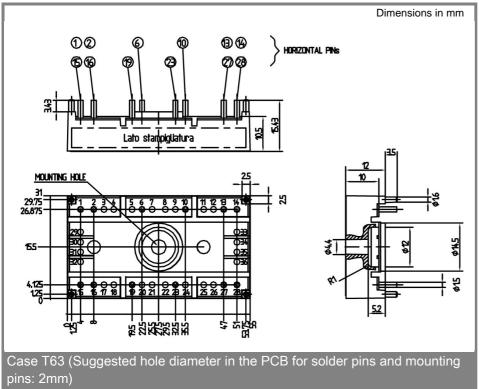


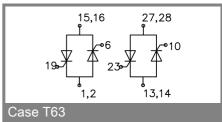




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